

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

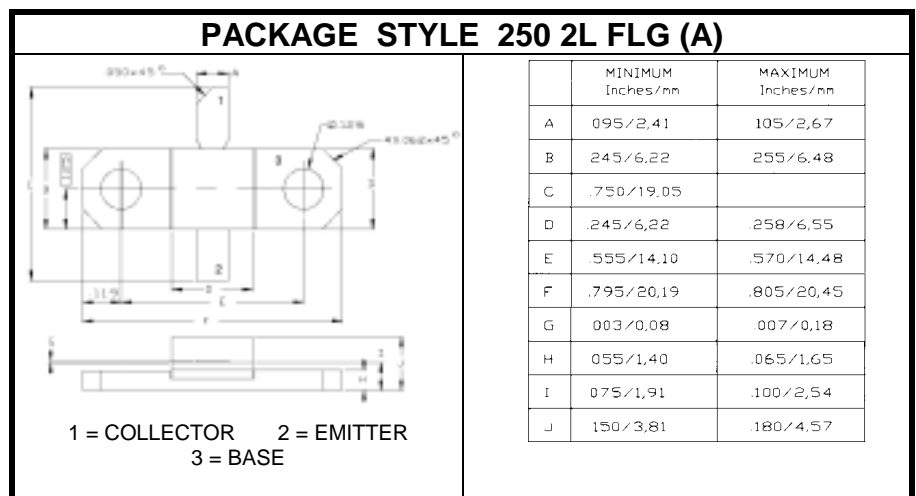
The **ASI SD1526-08** is a Common Base Device Designed for IFF, DME, and Tacan Pulse Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Low Thermal Resistance

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	45 V
P_{DISS}	21.9 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	8.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	45			V
BV_{CEO}	I _C = 5.0 mA	45			V
BV_{CES}	I _C = 5.0 mA	45			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CES}	V _{CE} = 28 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10		200	---
P_G	V _{CE} = 28 V P _{out} = 5.0 W PULSE WIDTH = 10 μS	9.5			dB
	f = 1025 to 1150 MHz DUTY CYCLE = 1.0%				